

Addressing Individual Atoms in Optical Lattices with Standing-Wave Driving Fields

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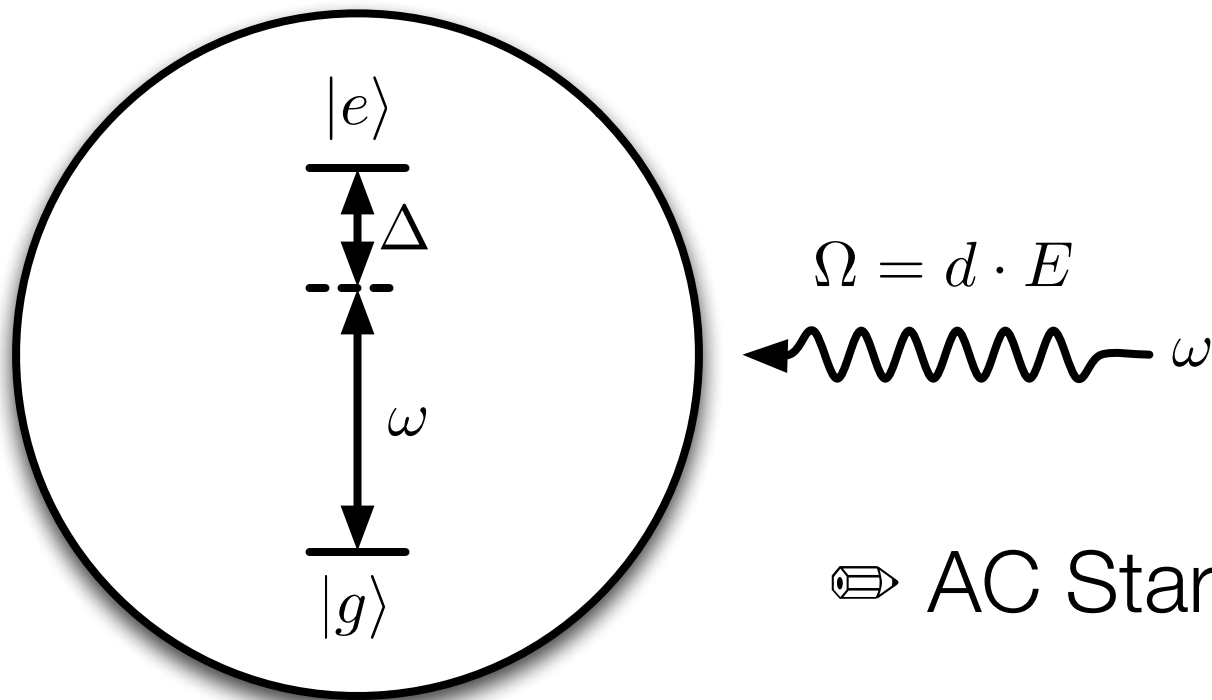
quant-ph/0703185, Phys. Rev. Lett. (in press)

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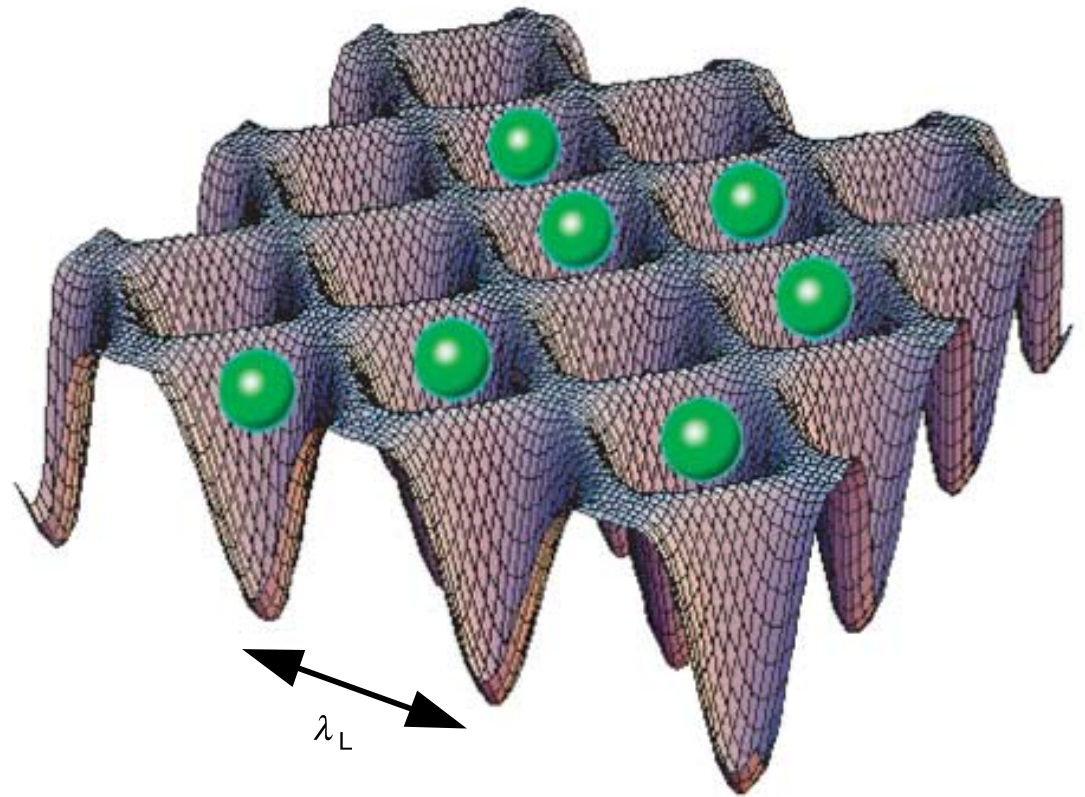
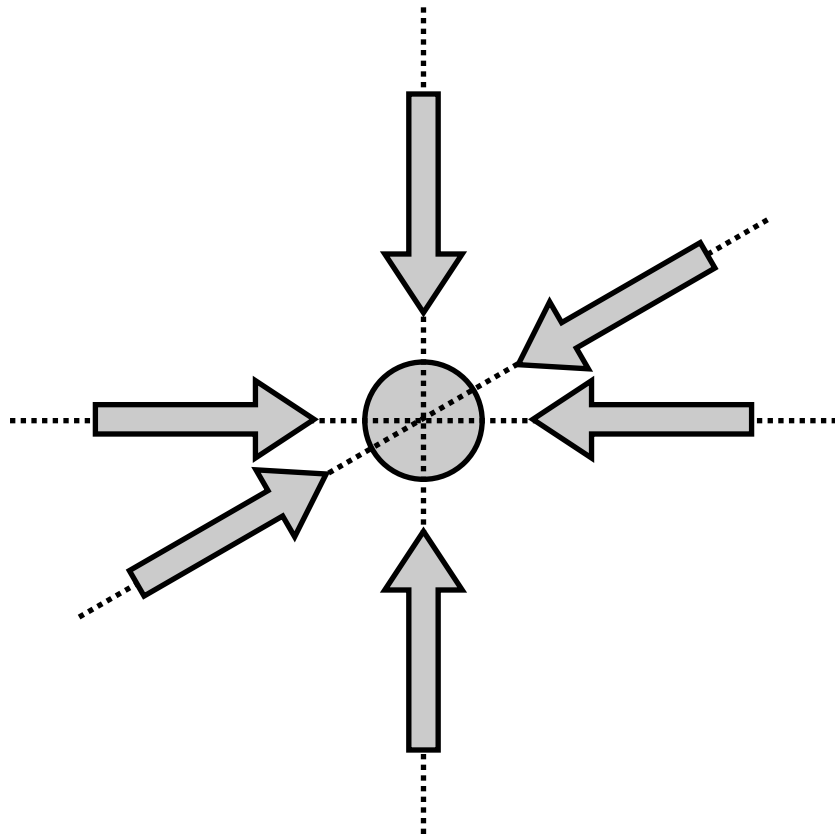
Light-induced potential



⇒ AC Stark shift ($\Delta \gg \Omega$)

$$V = -\frac{(d \cdot E)^2}{\Delta}$$

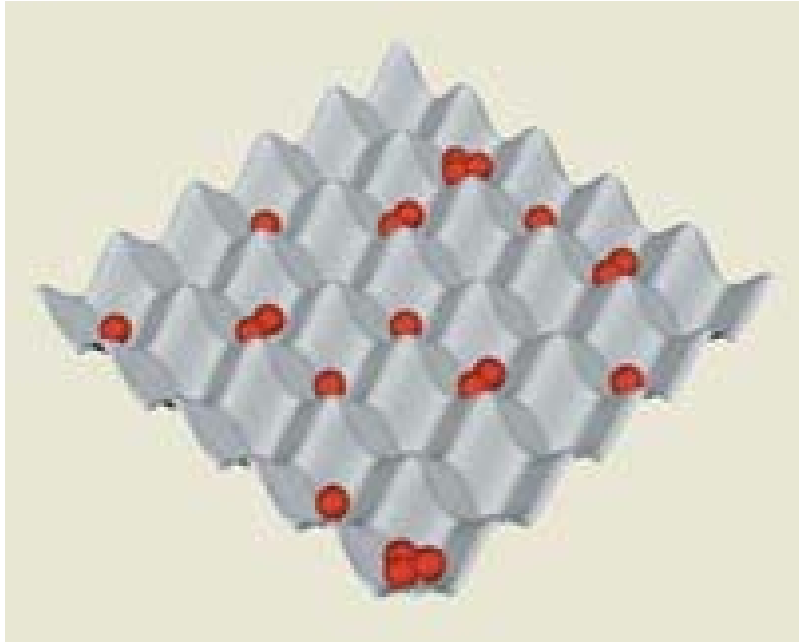
Optical lattice



Bose-Hubbard model

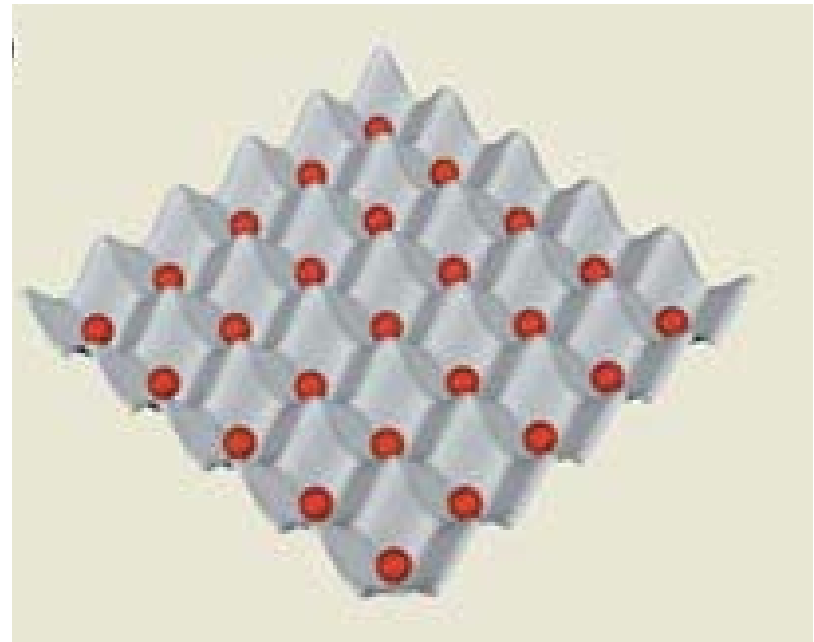
$$H = \underbrace{-J \sum_{\langle i,j \rangle} b_i^\dagger b_j}_{\text{tunneling}} + \underbrace{\frac{1}{2} U \sum_i \hat{n}_i (\hat{n}_i - 1)}_{\text{on site repulsion}} + \sum_i \epsilon_i \hat{n}_i$$

Superfluid-Mott insulator phase transition



$$J \gg U$$

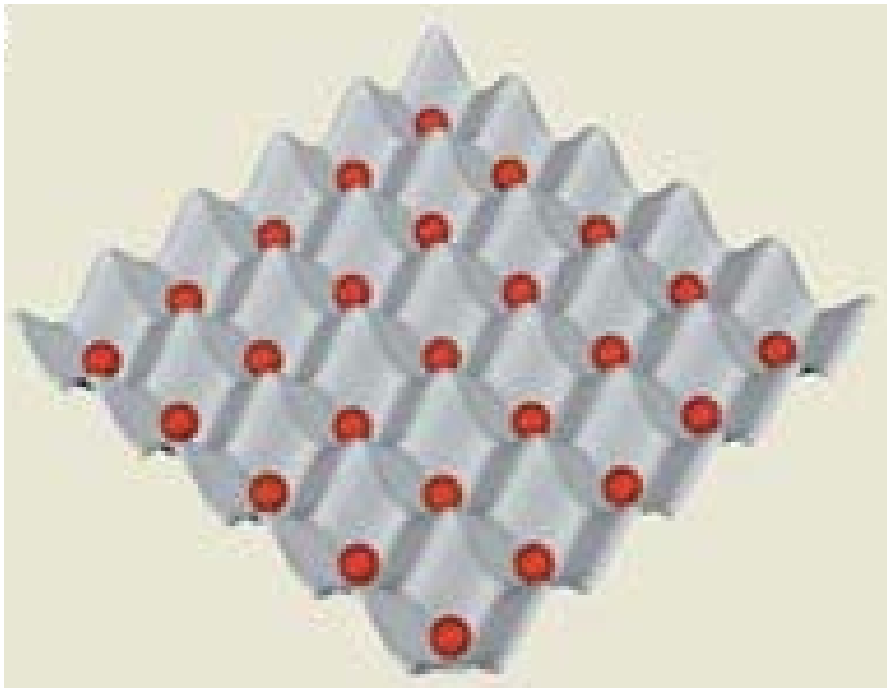
superfluid



$$J \ll U$$

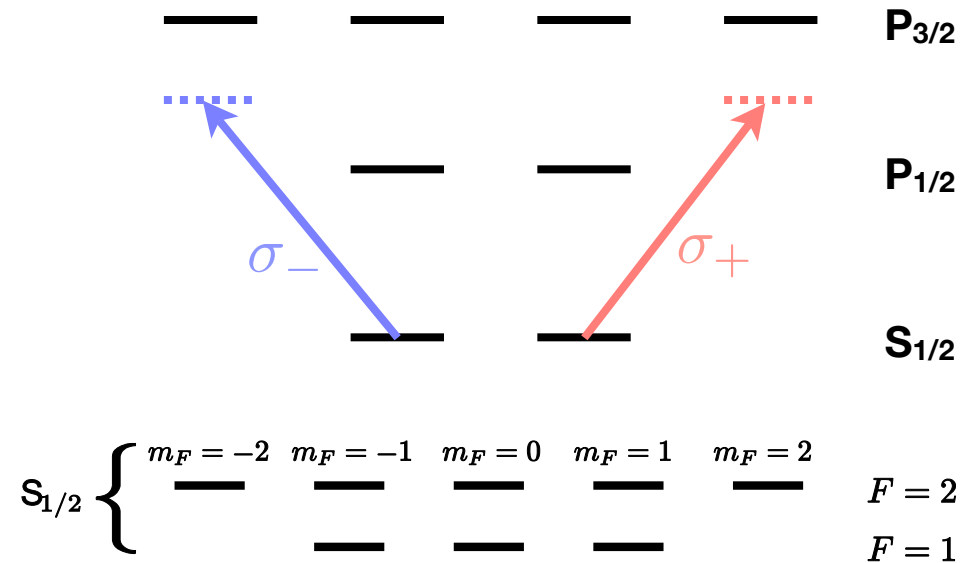
Mott insulator

Quantum register array



- ⇒ unitary operation?
- ⇒ measurement?

State-dependent lattice potential

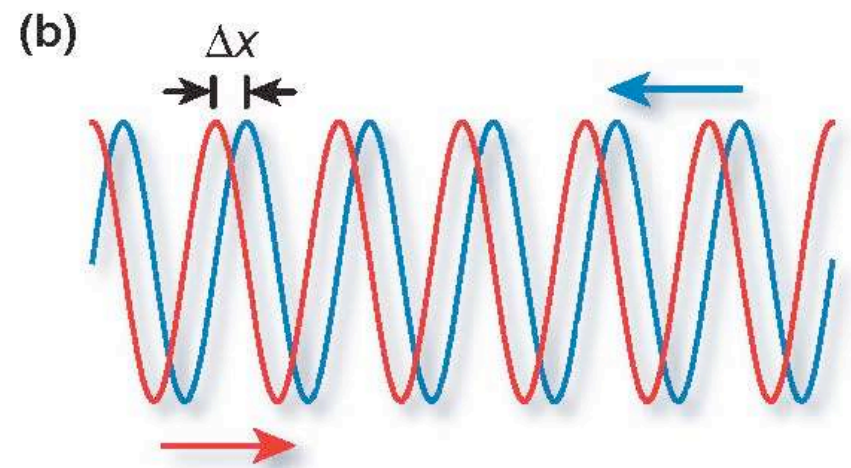
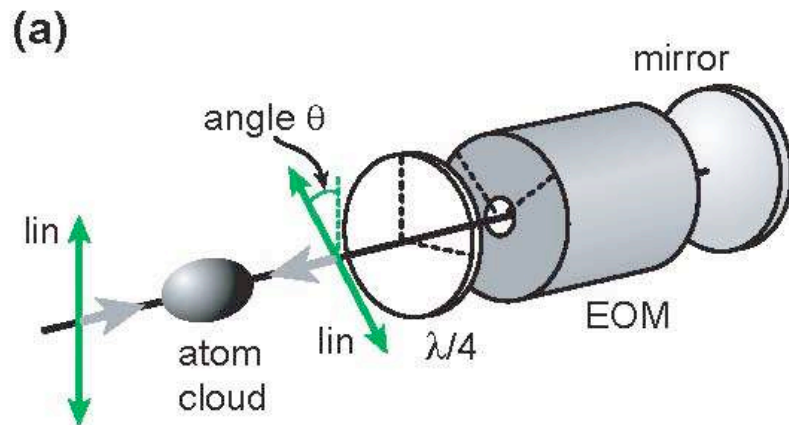


$$V_{|F=2, m_F=2\rangle}(x) = V_+(x)$$

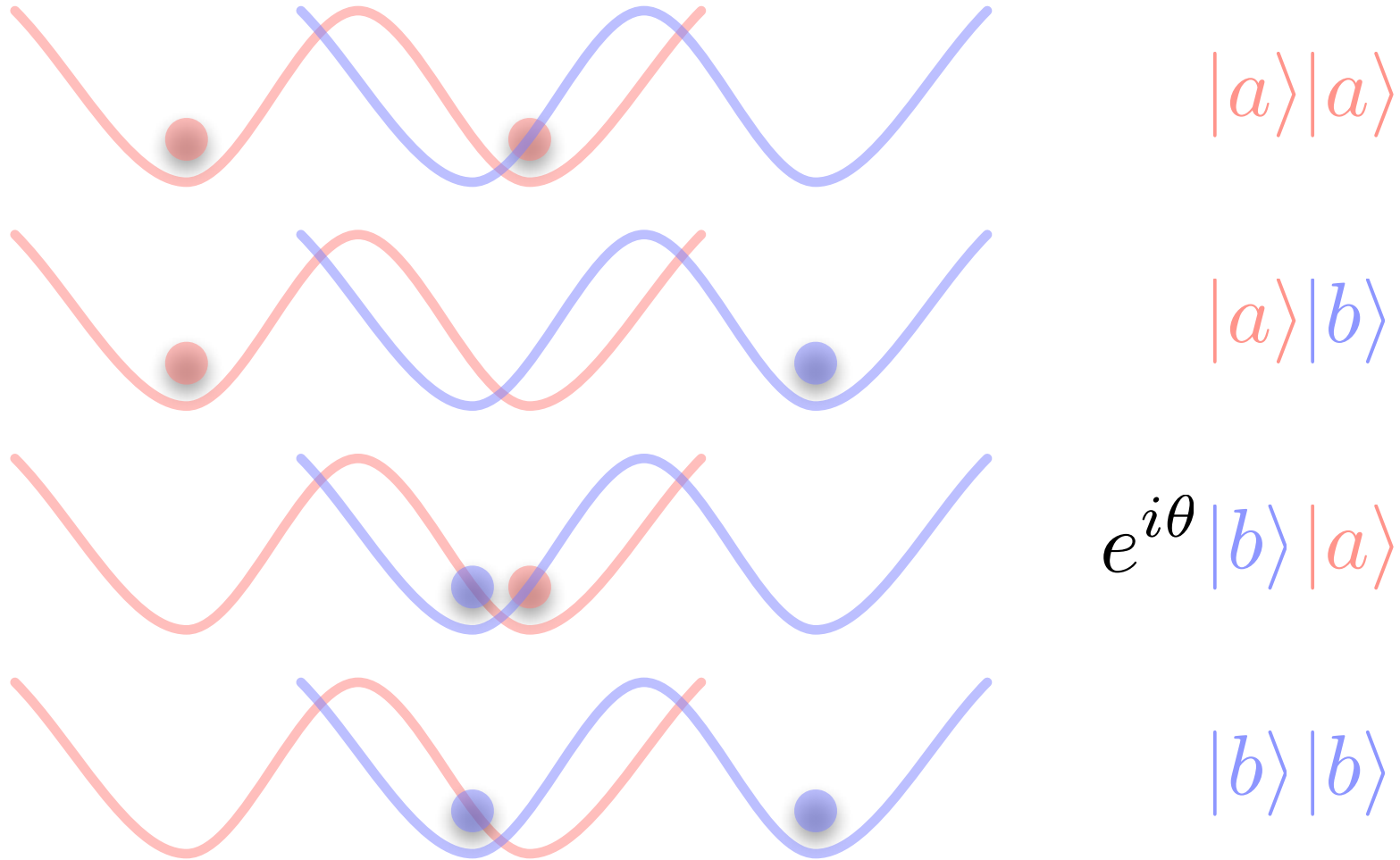
$$V_{|F=1, m_F=1\rangle}(x) = \frac{3}{4}V_+(x) + \frac{1}{4}V_-(x)$$

$$V_{|F=1, m_F=-1\rangle}(x) = \frac{1}{4}V_+(x) + \frac{3}{4}V_-(x)$$

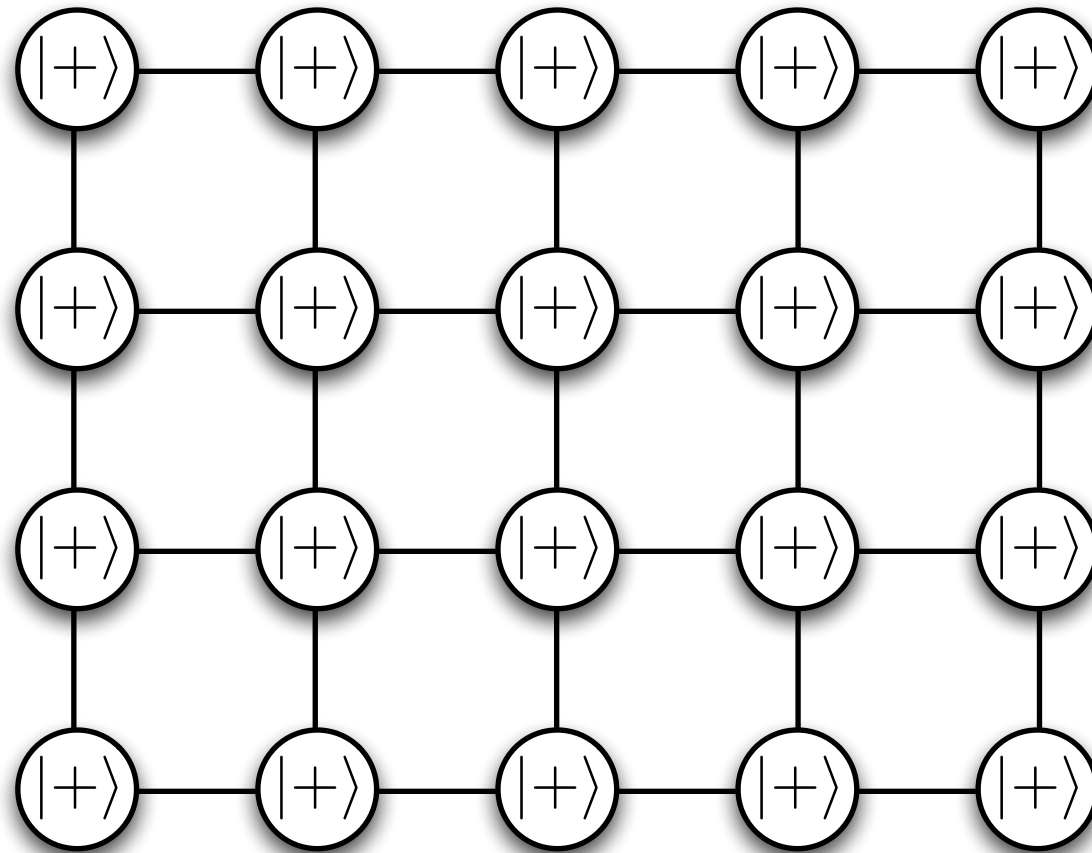
State-dependent lattice potential



Controlled-phase operation

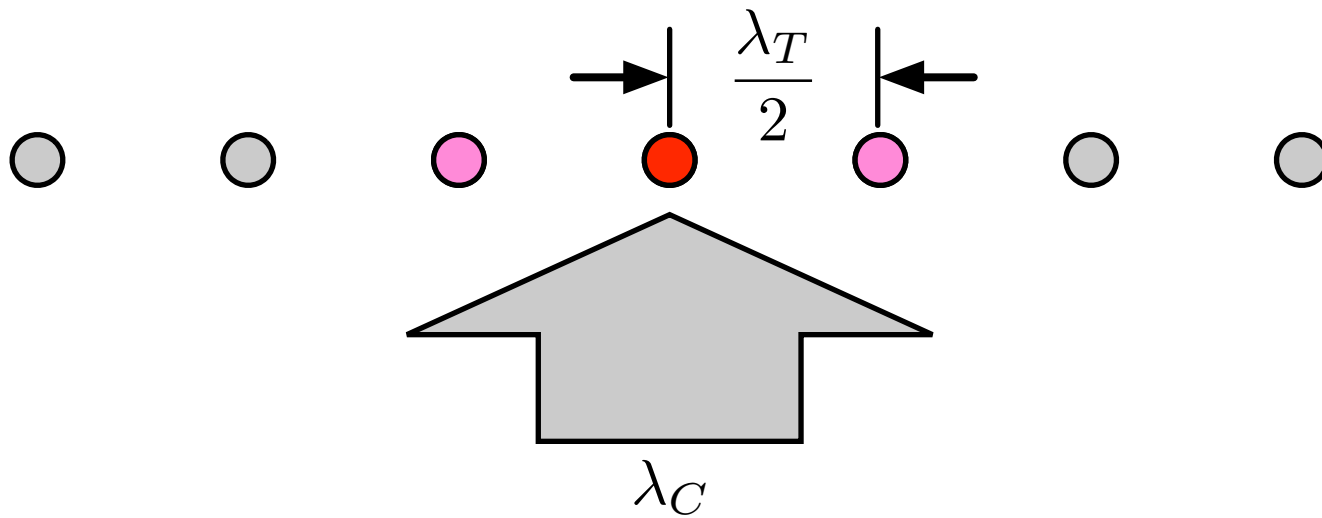


Cluster state



 single-qubit operation?

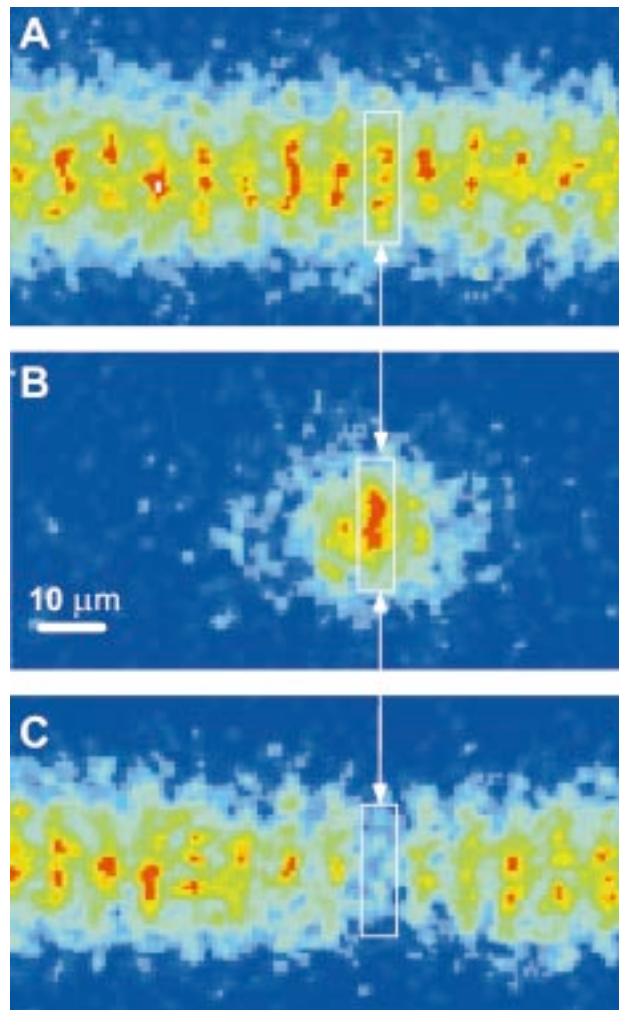
Individual-atom addressing



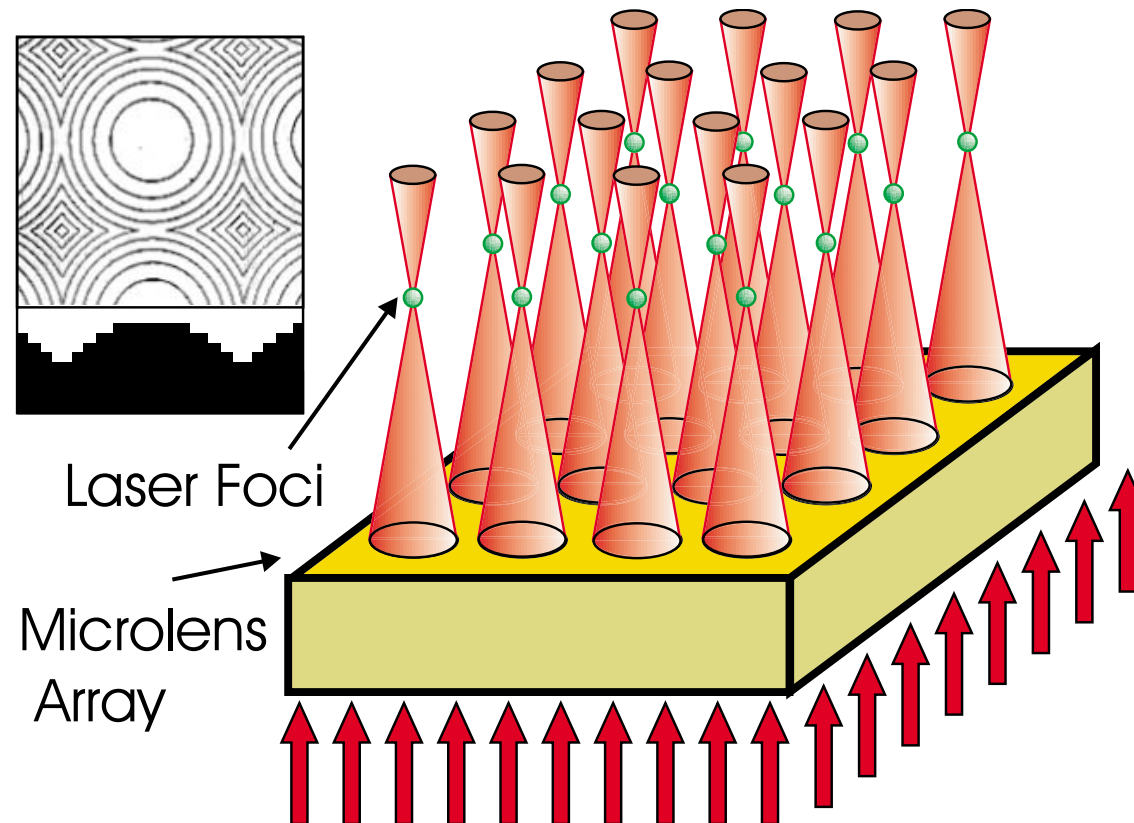
$$\lambda_C \gtrsim \lambda_T$$

diffraction limit!

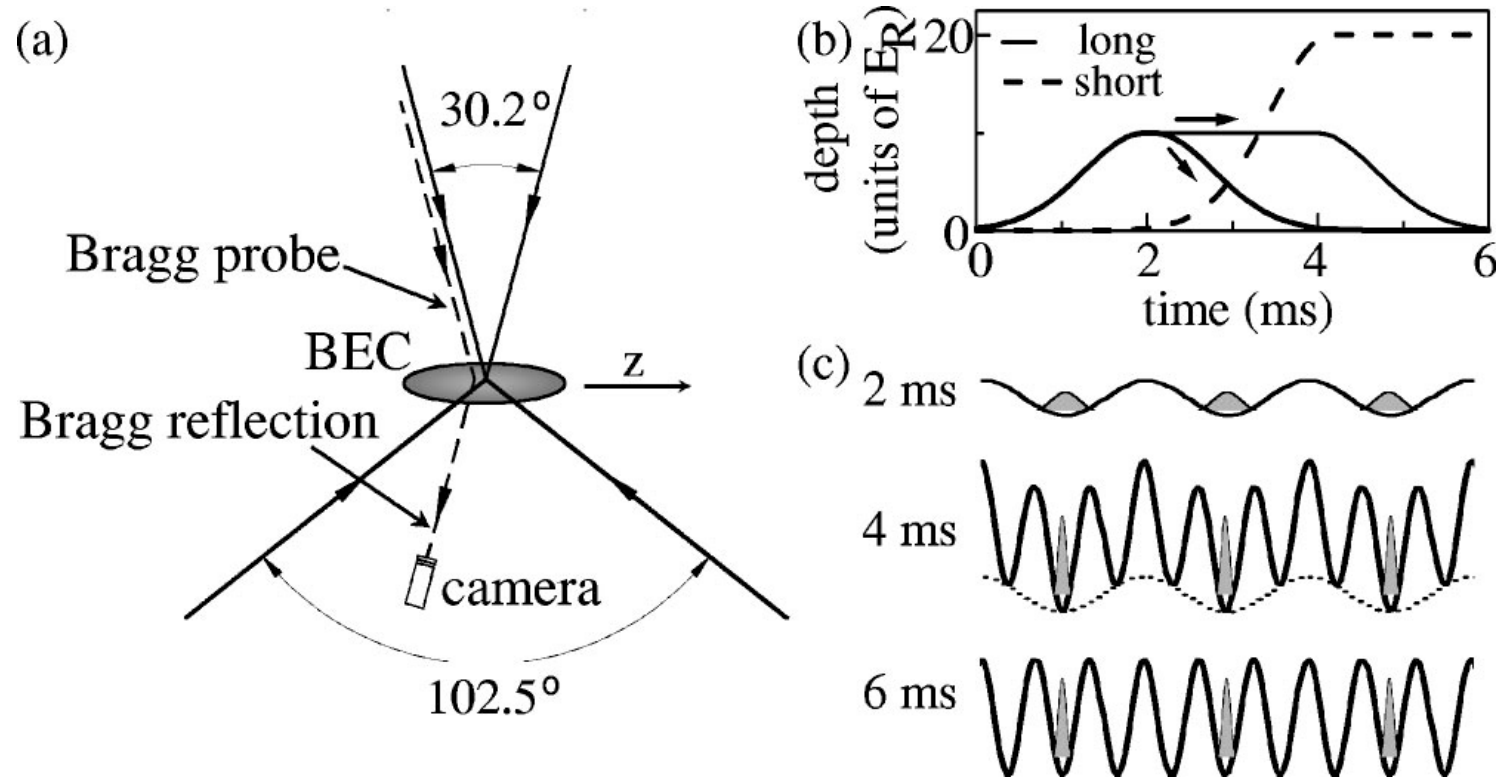
CO₂ laser optical lattice



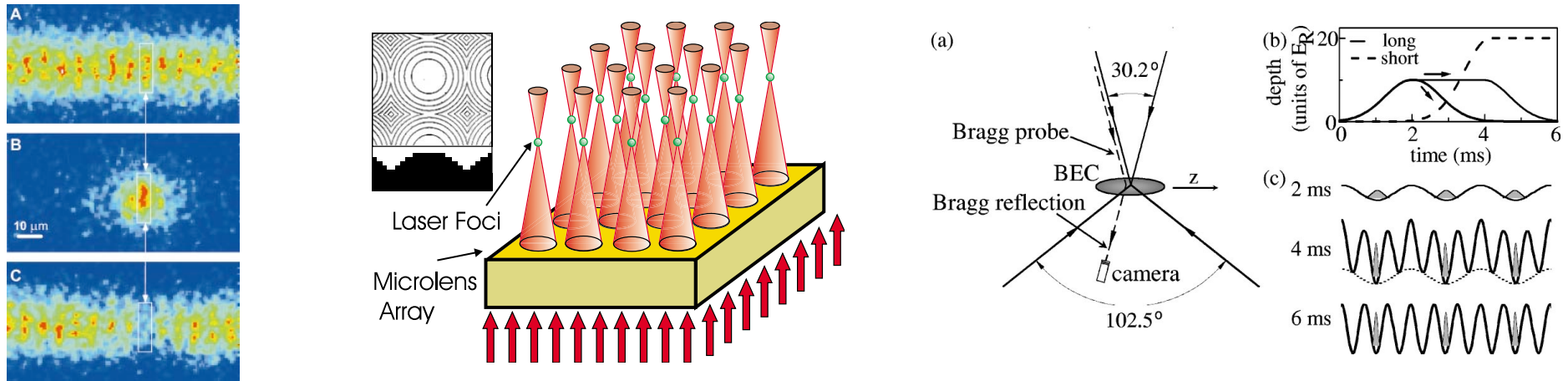
Micro-trap array



Patterned loading of an optical lattice



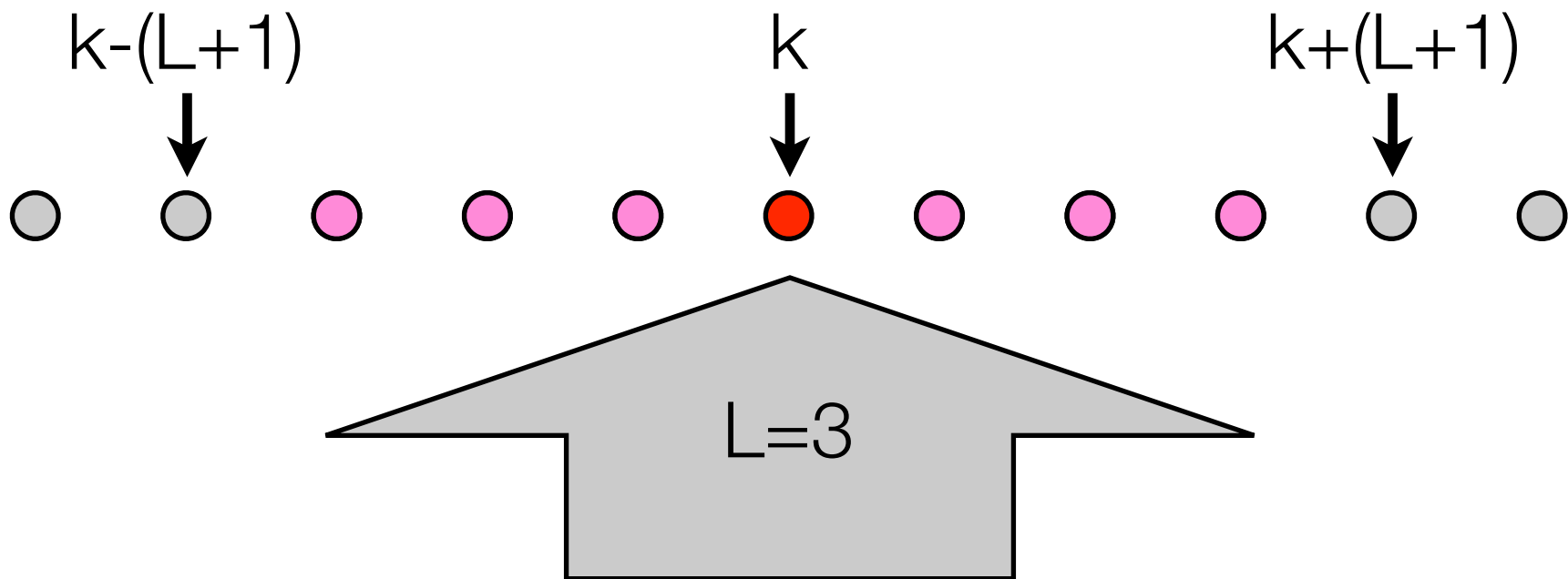
Individual-atom addressing?



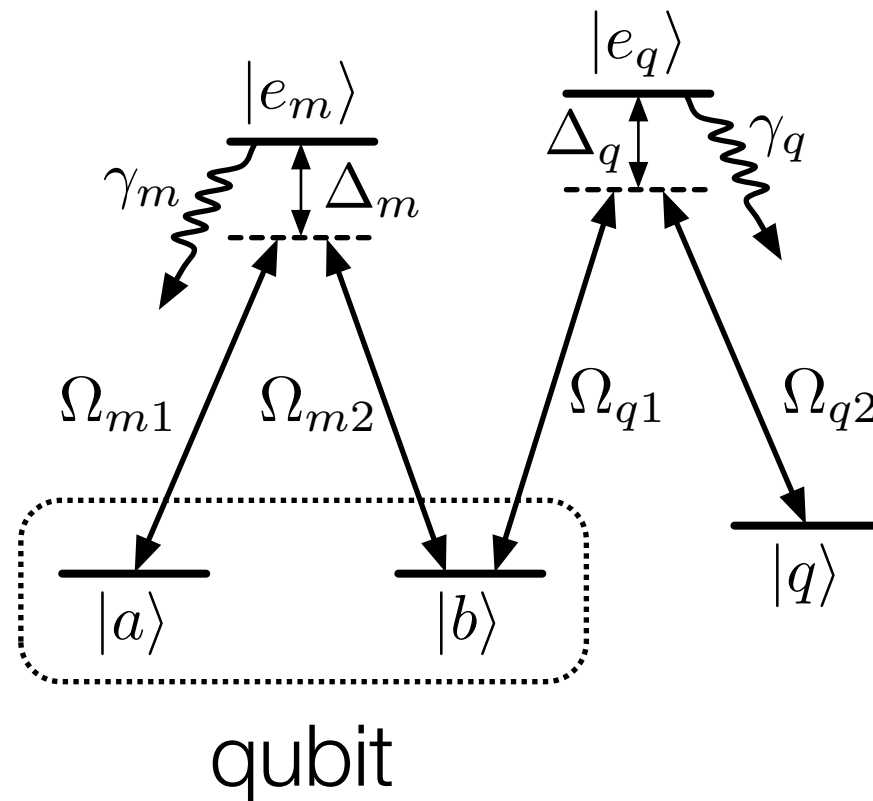
- One atom per site? Two-qubit operation?
- Other methods: external field, pointer atom, ...
 - Complexity? Precision?

Scheme

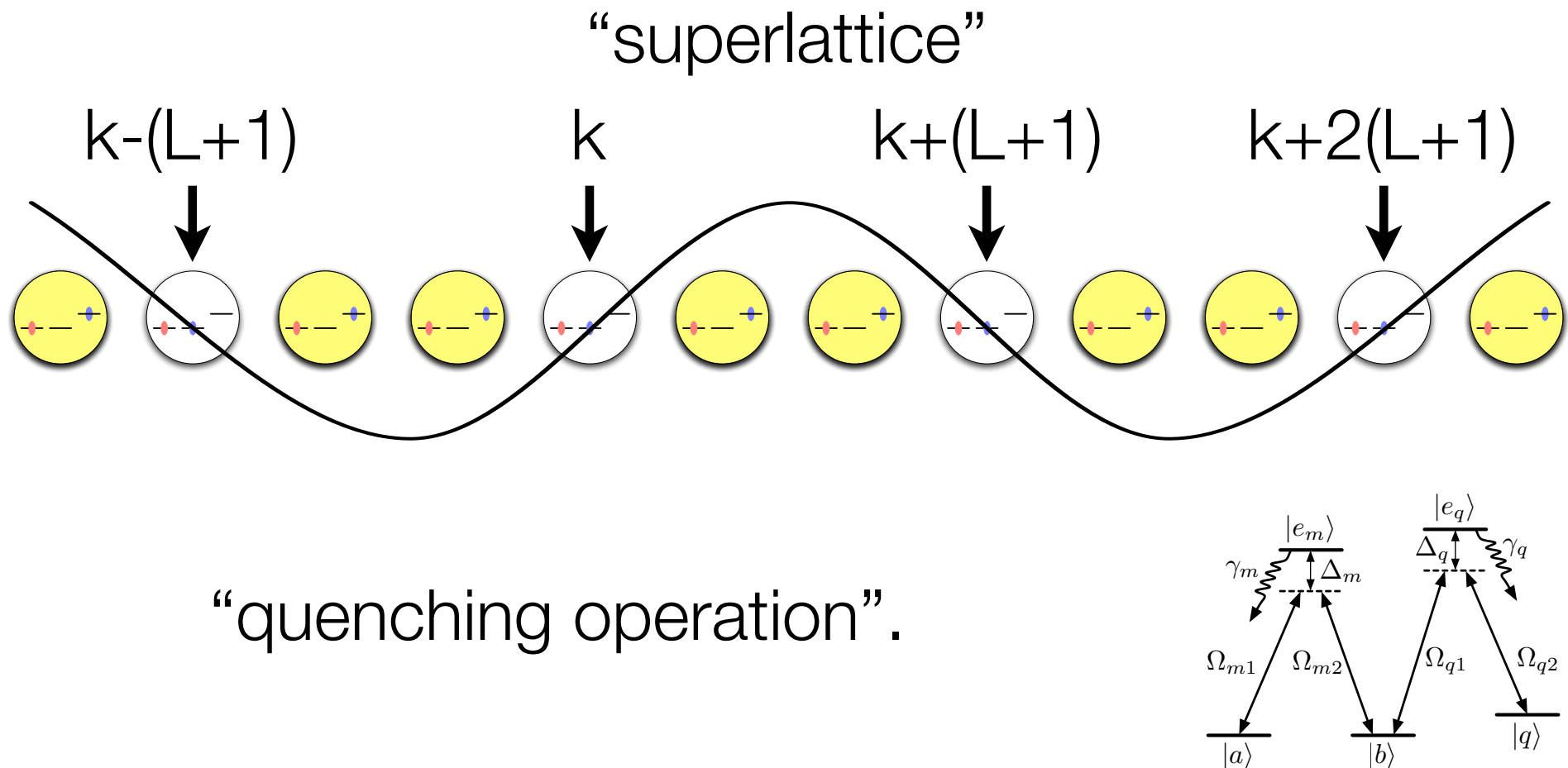
Assumption



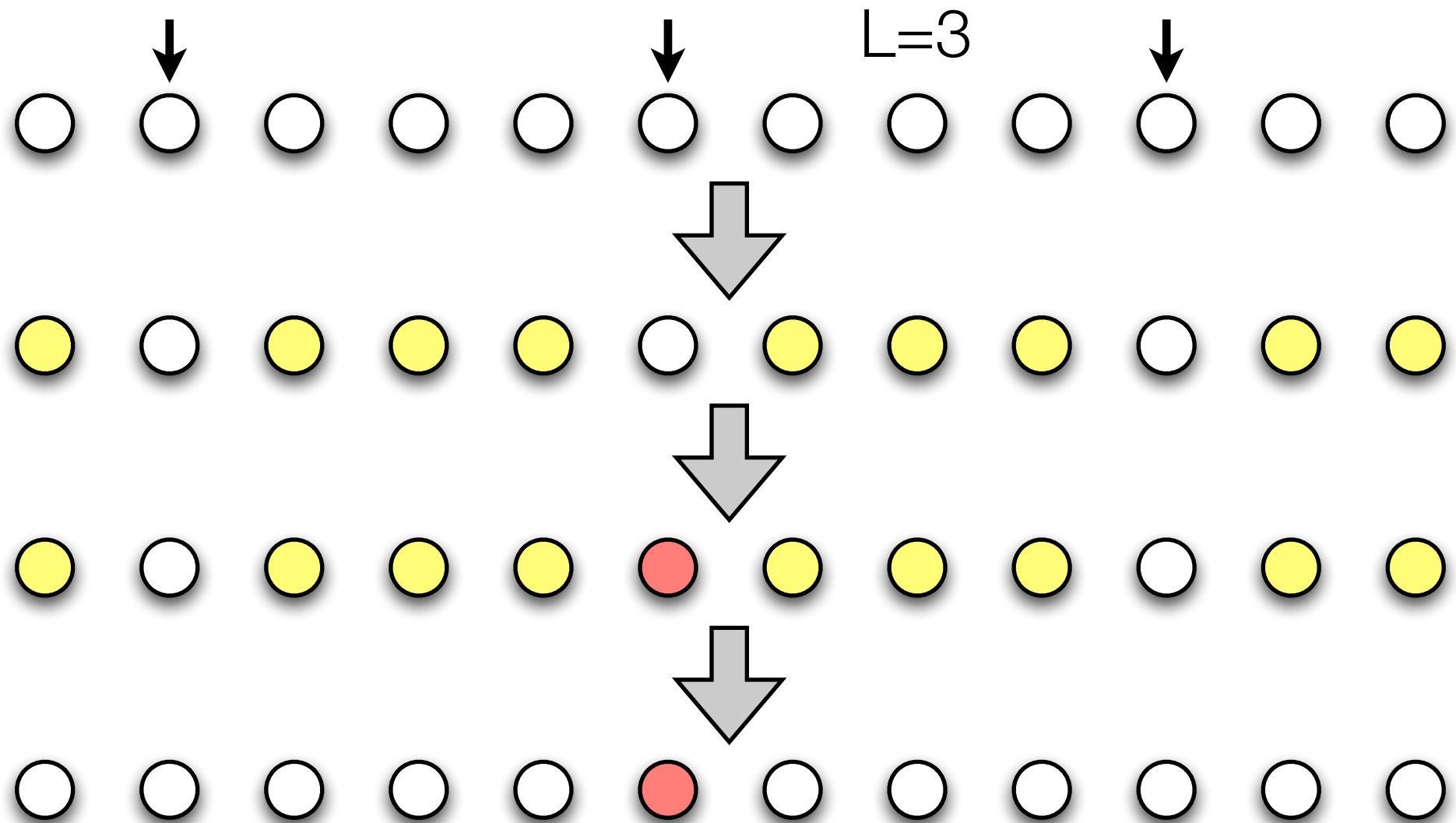
Atomic levels and transitions



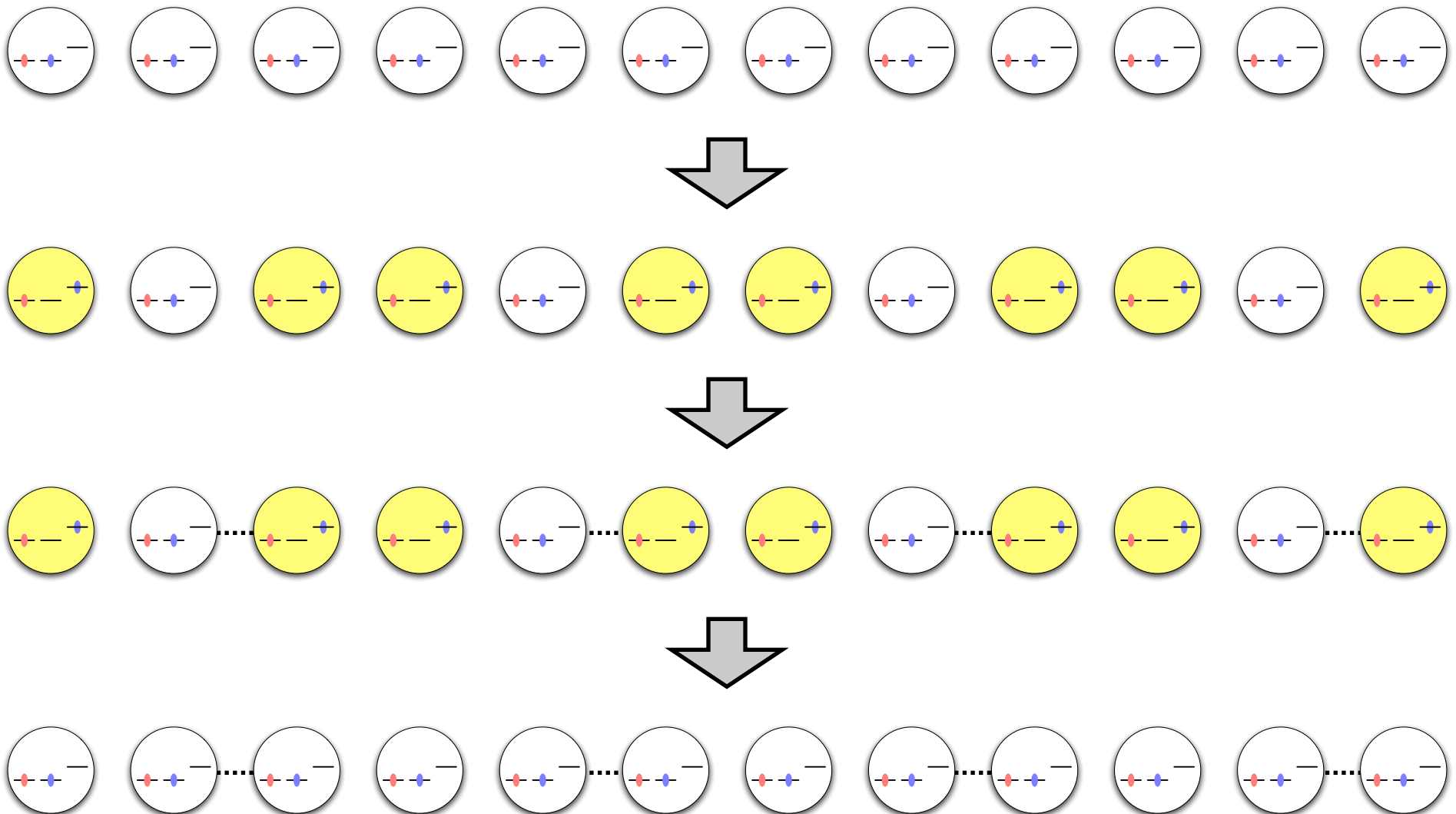
Position-dependent atomic population transfer



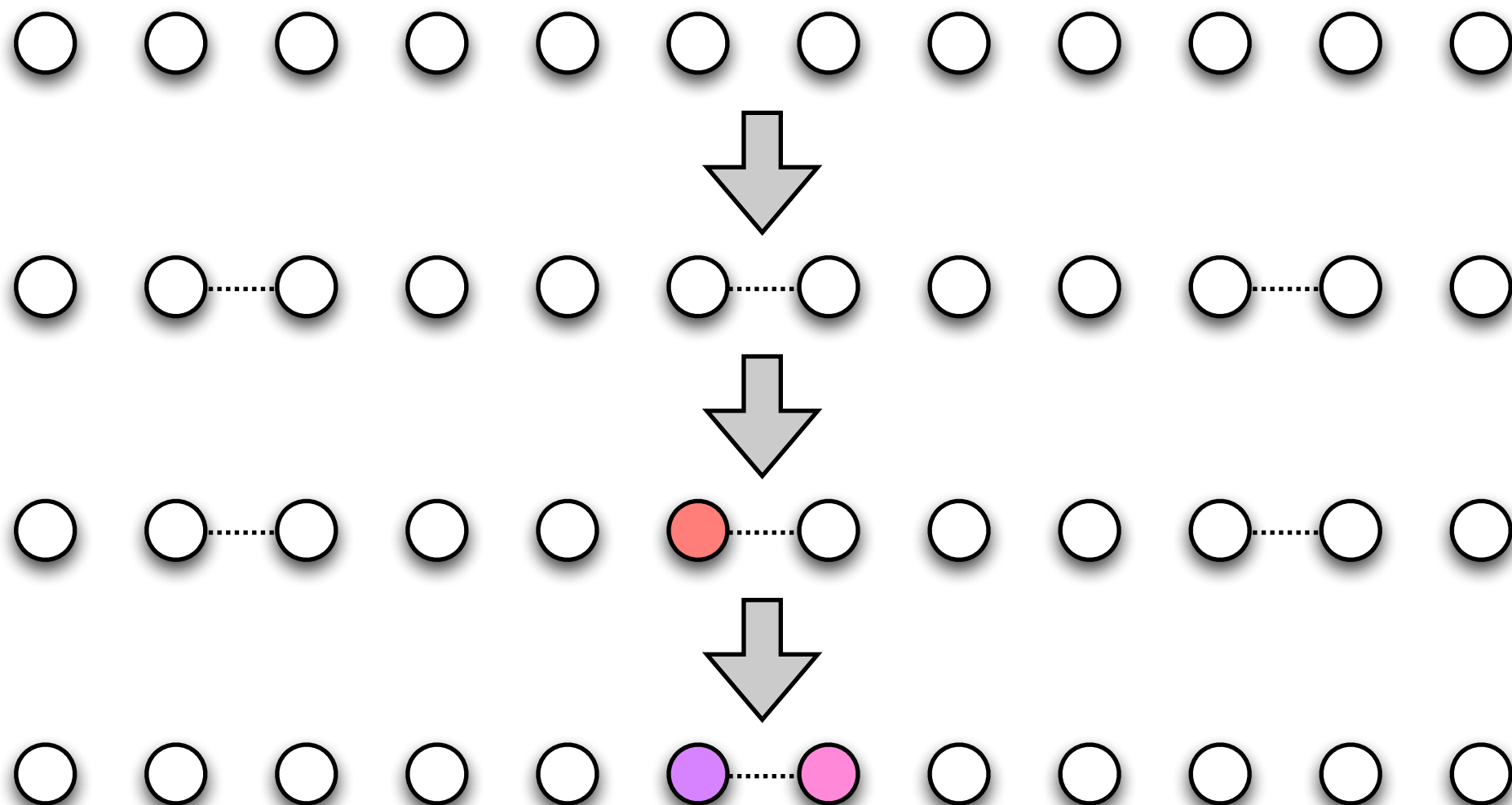
Single-atom addressing



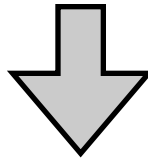
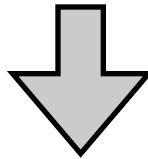
Collective two-qubit operation



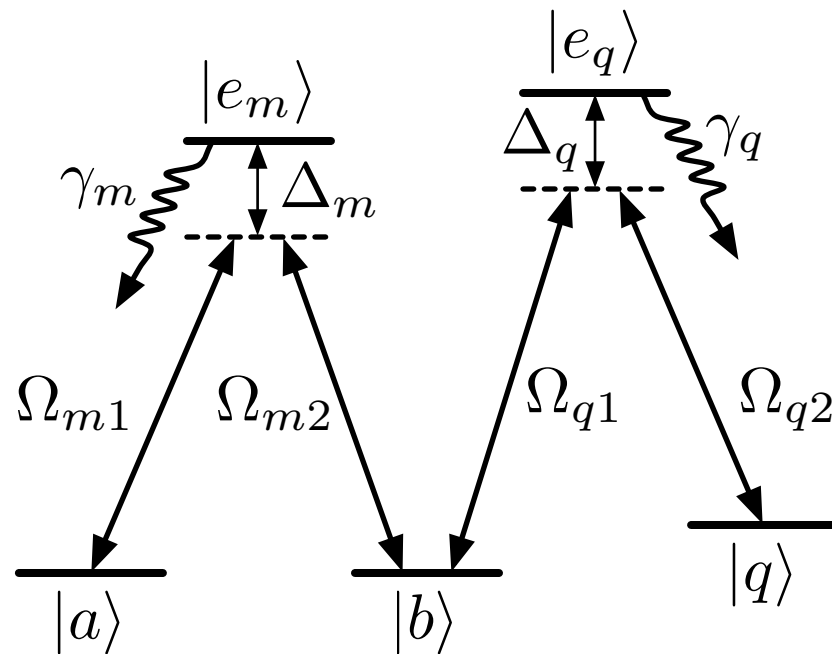
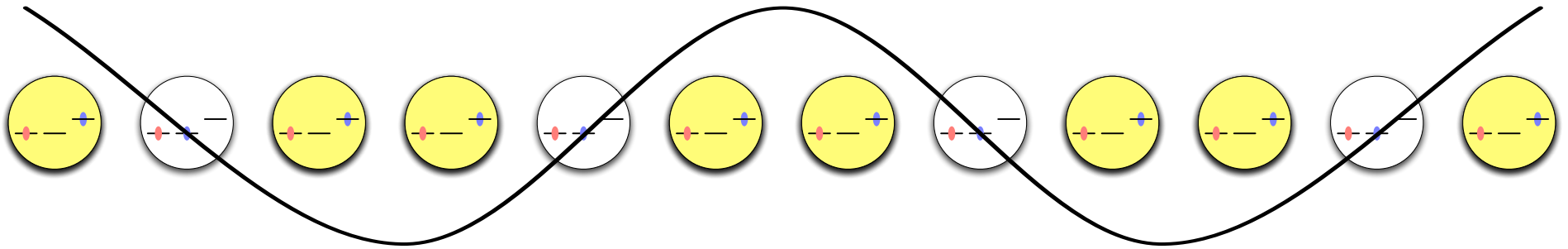
Selective two-qubit operation



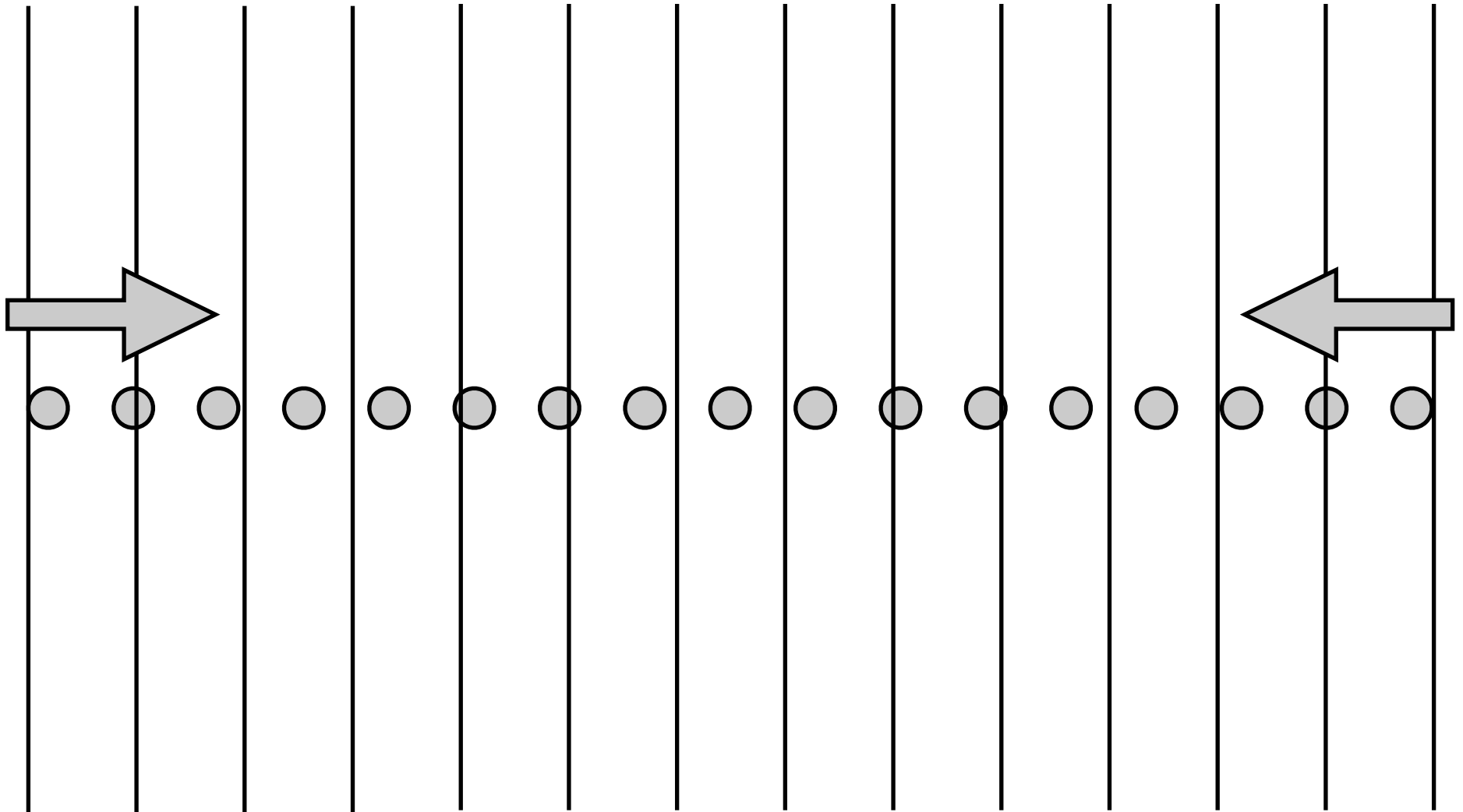
Patterned loading



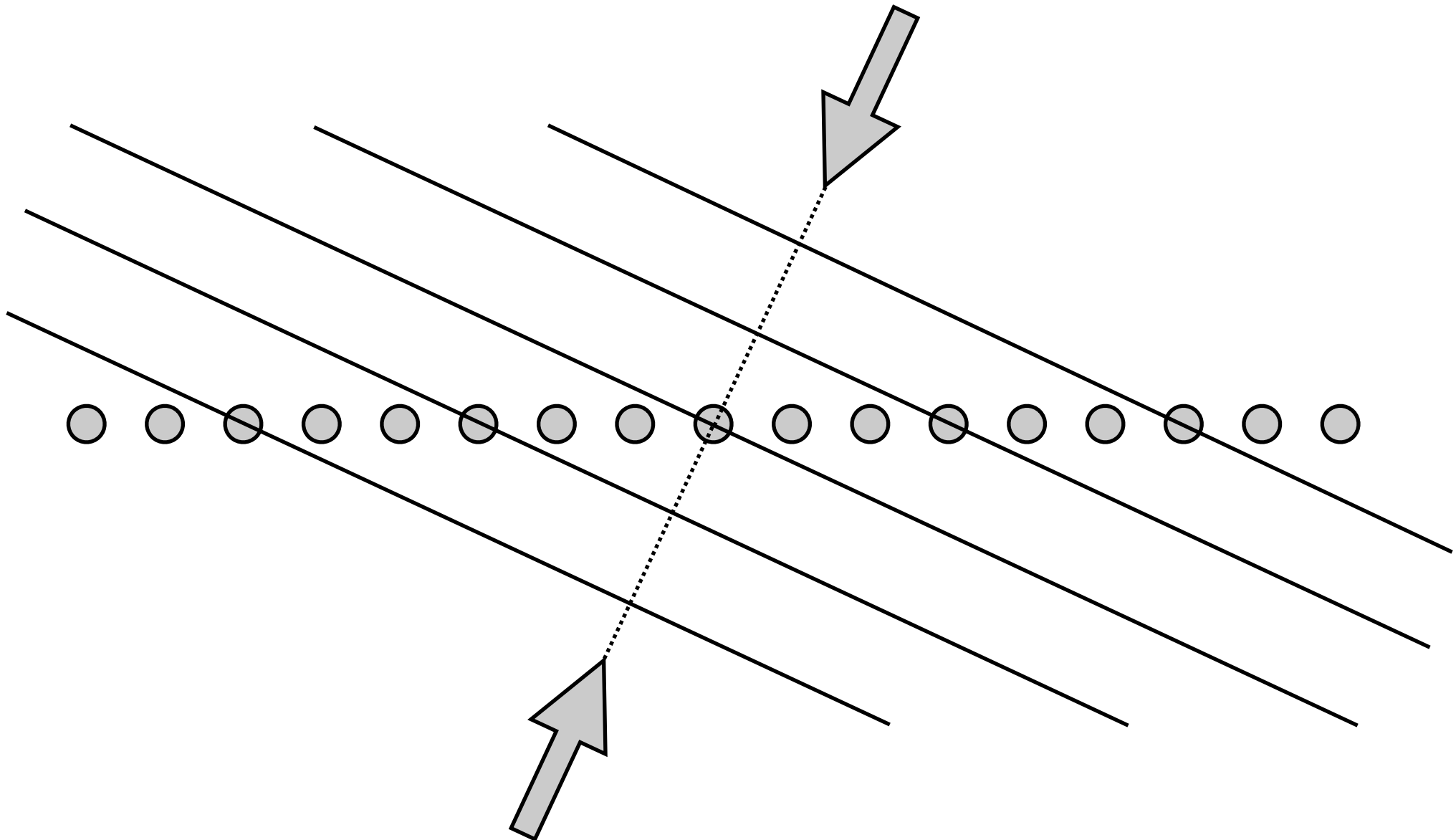
Quenching operation?



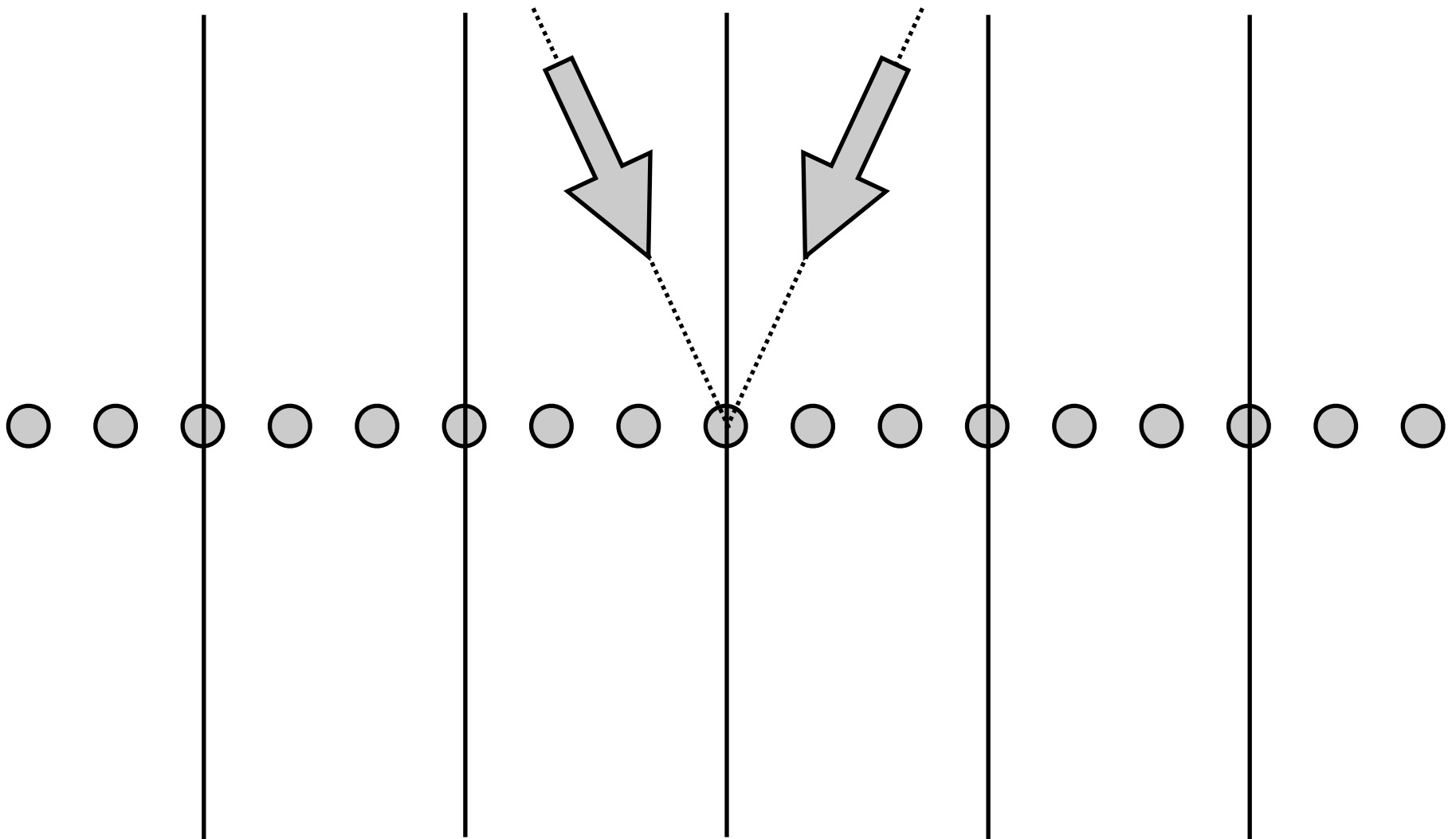
Arbitrary standing-wave field



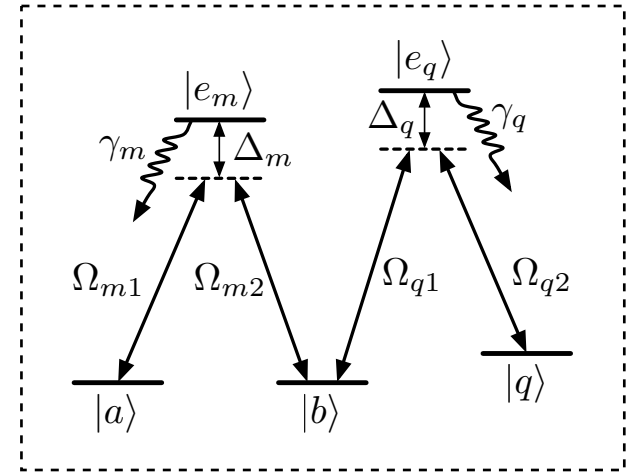
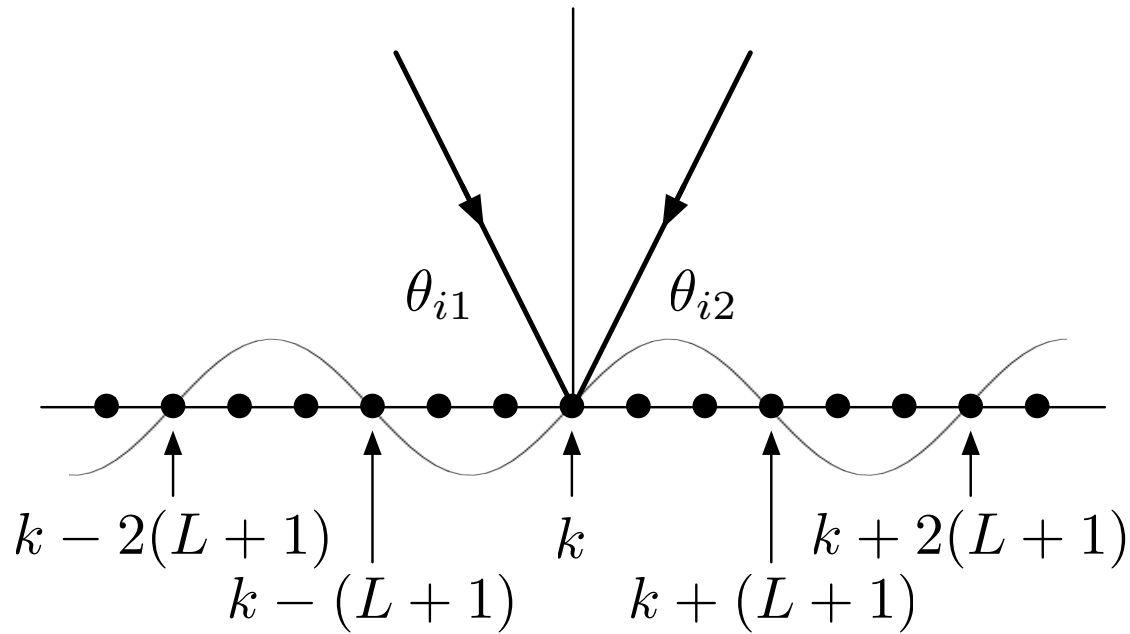
Arbitrary standing-wave field



Arbitrary standing-wave field

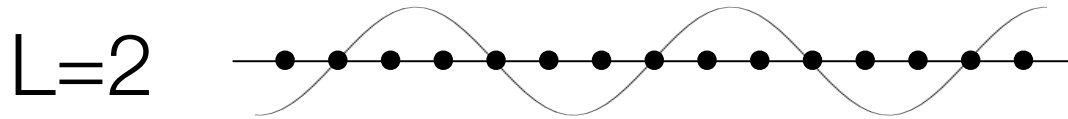
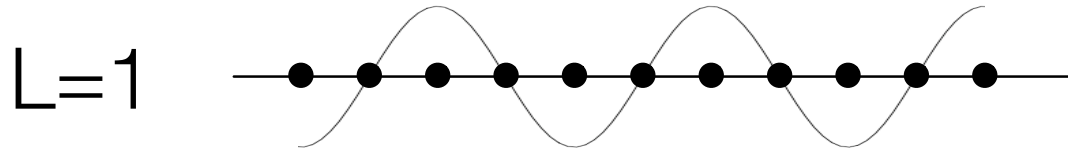


Standing-wave driving field



$$\Omega_{qi}^{(s)}(t) = e^{-\eta^2/2} \Omega_0 \sin \left(\pi \frac{s - k}{L + 1} \right) \Omega_i(t)$$

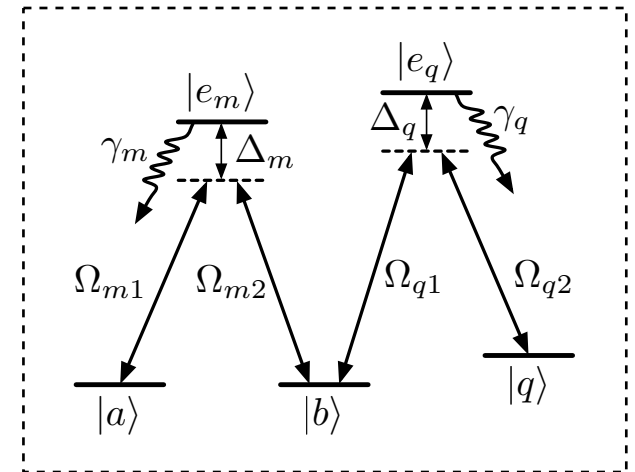
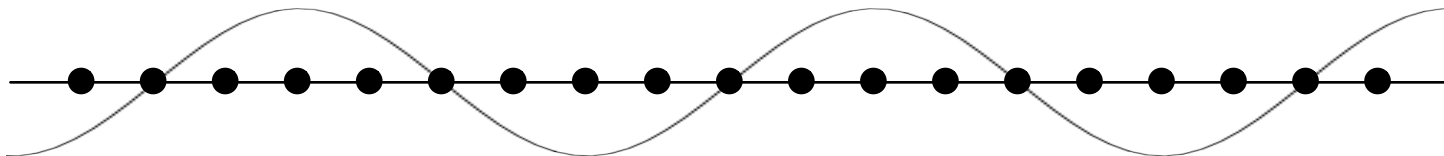
Standing-wave driving field



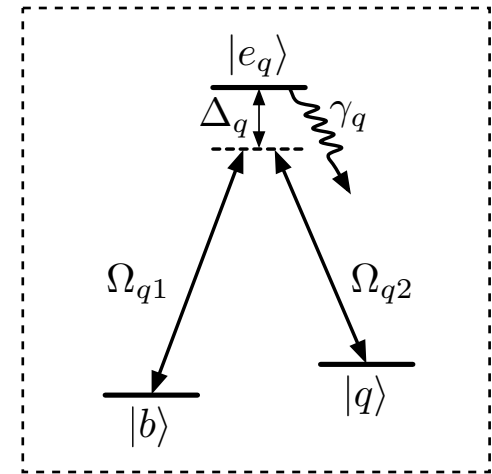
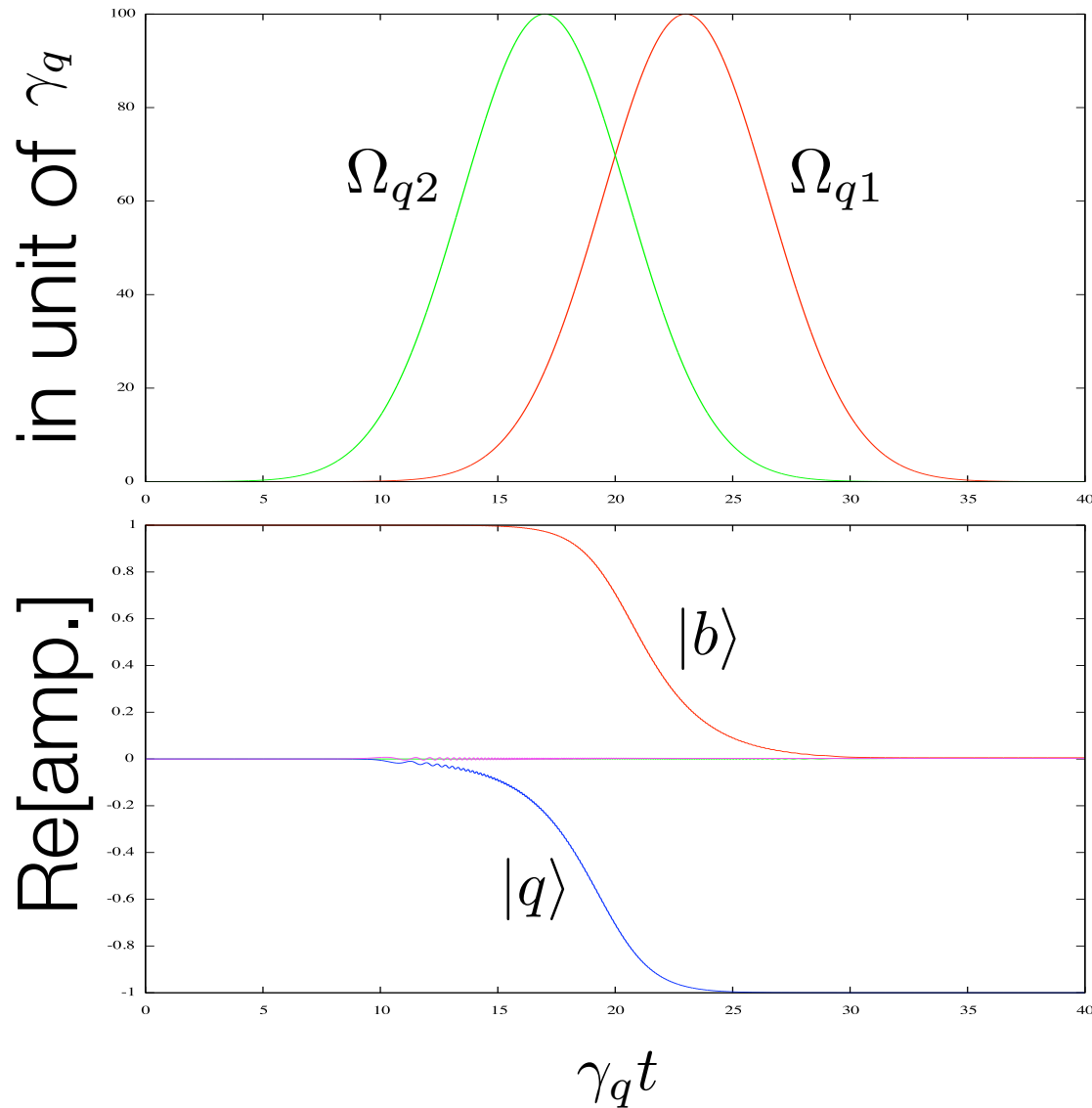
⇒ Raman transition ($\Delta_q \gg |\Omega_{qi}^{(s)}|$)

$$\Omega^{(s)} = \frac{\Omega_{q1}^{(s)} \Omega_{q2}^{(s)}}{\Delta_q}$$

⇒ When $L=3,4,5,\dots$?

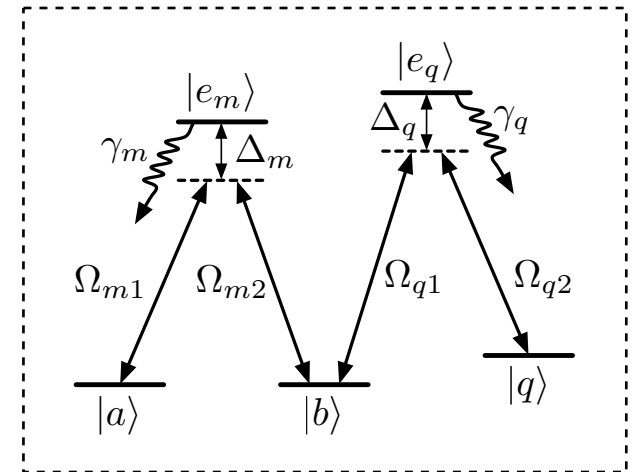
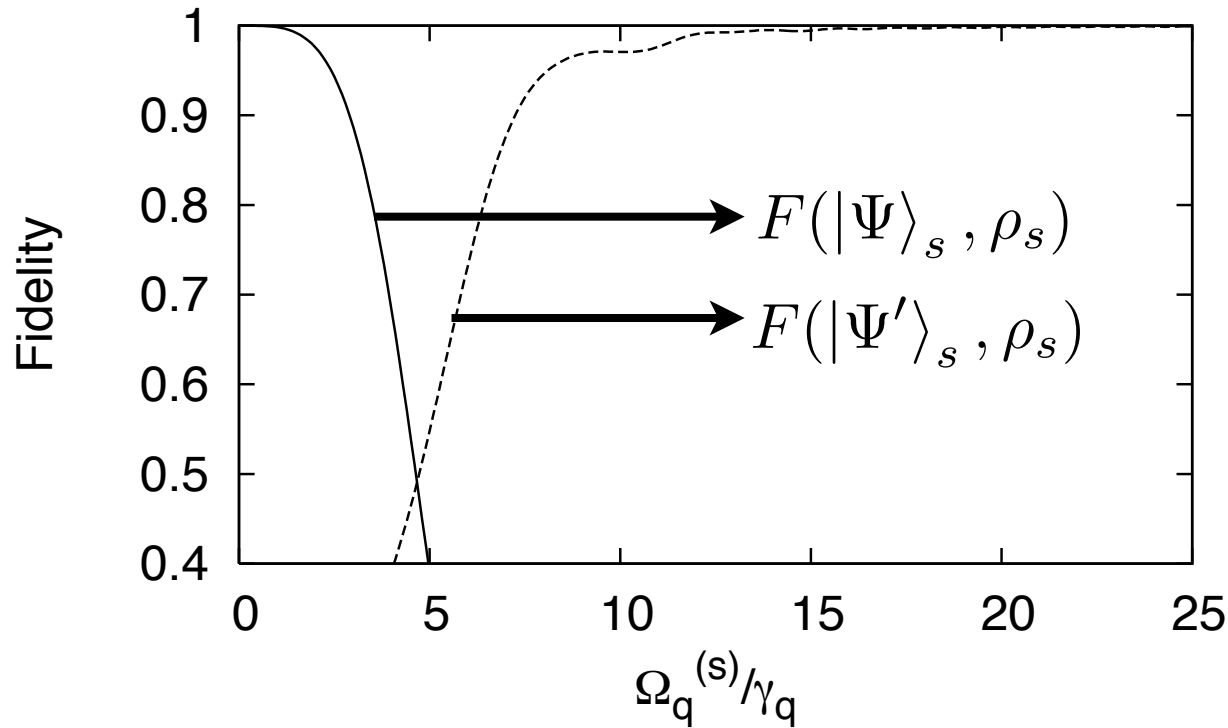


Stimulated Raman Adiabatic Passage (STIRAP)



$$\Delta_q = 100\gamma_q$$

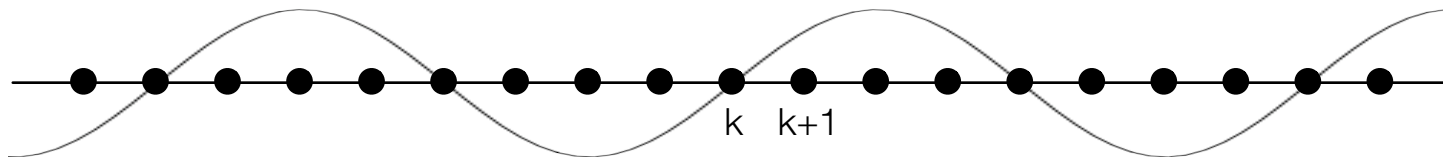
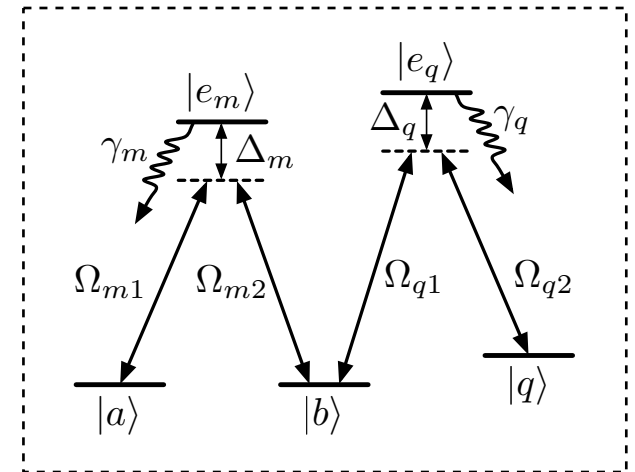
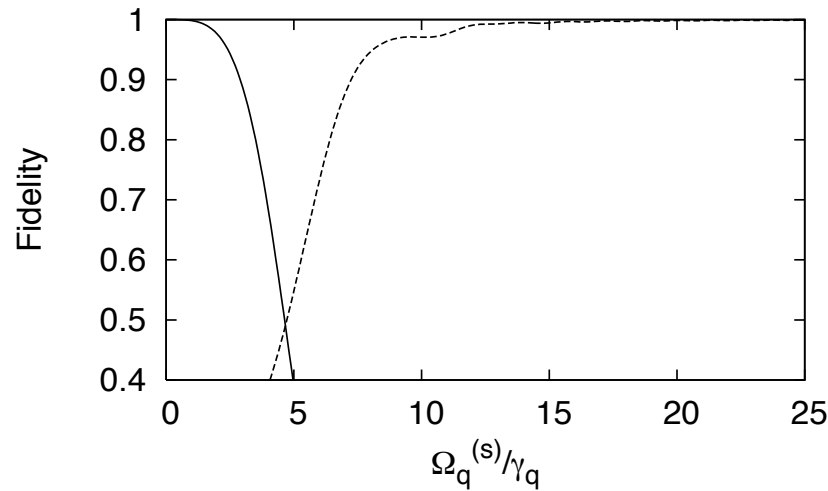
Stimulated Raman Adiabatic Passage (STIRAP)



$$|\Psi\rangle_s = \frac{1}{\sqrt{2}}(|a\rangle_s + |b\rangle_s) \rightarrow |\Psi'\rangle_s = \frac{1}{\sqrt{2}}(|a\rangle_s + |q\rangle_s)$$

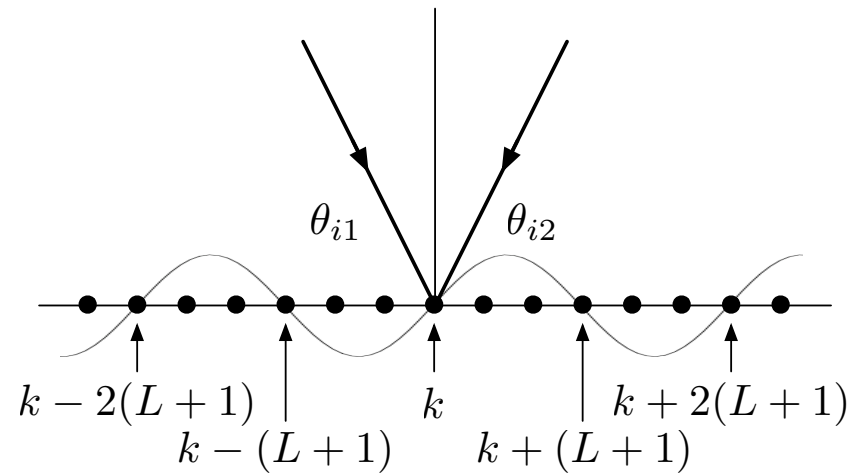
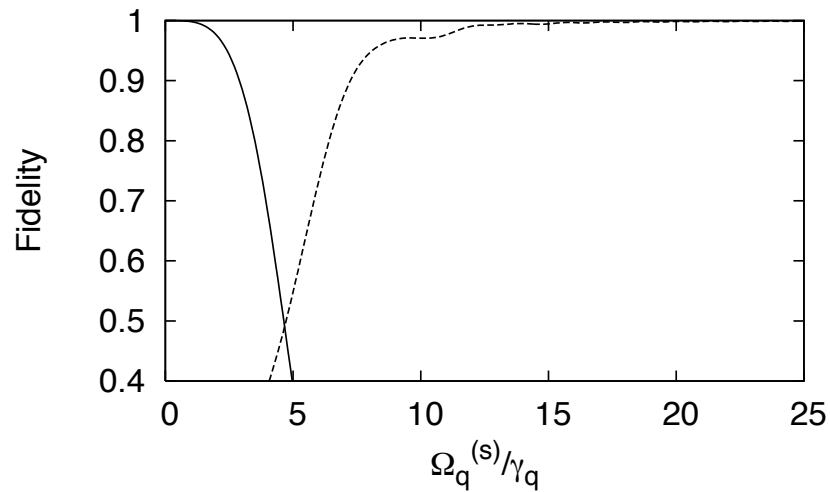
$\searrow \rho_s$

Quenching operation for an arbitrary L



We take $\Omega_q^{(k+1)} > (\text{threshold})$.

Required precision



$$(L+1)(N\Delta\theta + \Delta\phi/\pi) \lesssim \text{const.}$$

(N: # of atoms)

Conclusion

- Simple scheme for addressing individual atoms in one- or two-dimensional optical lattices.
- It allows single-atom operations, two-atom operations, patterned loading, and so on.
- It is robust against considerable imperfections and actually within current technology.